
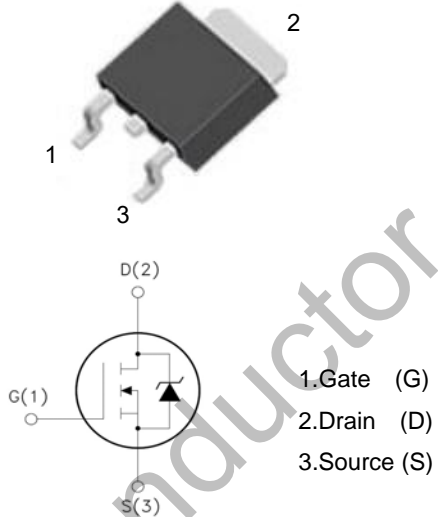
 <p>WGD100N03</p> <p>30V N-Channel MOSFET</p> <p>Features:</p> <ul style="list-style-type: none"> <input type="checkbox"/> Low Intrinsic Capacitances. <input type="checkbox"/> Excellent Switching Characteristics. <input type="checkbox"/> Extended Safe Operating Area. <input type="checkbox"/> Unrivalled Gate Charge :Qg= 40nC (Typ.). <input type="checkbox"/> BVDSS=30V, I_D= 100A <input type="checkbox"/> R_{DS(on)} : 5.0mΩ (Typ) @V_G=10V <input type="checkbox"/> 100% Avalanche Tested 	<p>TO-252 </p>  <p>1.Gate (G) 2.Drain (D) 3.Source (S)</p>
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Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	100	A
Drain Current-Continuous(T _C =100°C)	I _D (100°C)	59	A
Pulsed Drain Current	I _{DM}	360	A
Maximum Power Dissipation	P _D	68	W
Single pulse avalanche energy ^(Note 5)	E _{AS}	95	mJ
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 To 175	°C

Thermal Characteristics

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	2.2	°C/W
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Electrical Characteristics (TA=25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30V, V_{GS}=0V,$	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	$V_{GS}=10V, I_D=20A$	-	5.0	5.5	m Ω
		$V_{GS}=4.5V, I_D=20A$	-	6.7	9.5	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V,$ $f=1.0MHz$	-	2100	-	pF
C_{oss}	Output Capacitance		-	326	-	pF
C_{rss}	Reverse Transfer Capacitance		-	282	-	pF
Q_g	Total Gate Charge	$V_{DS}=15V, I_D=30A,$ $V_{GS}=10V$	-	45	-	nC
Q_{gs}	Gate-Source Charge		-	3	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	15	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=15V,$ $I_D=30A, R_{GEN}=3\Omega,$ $V_{GS}=10V$	-	21	-	ns
t_r	Turn-on Rise Time		-	32	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	59	-	ns
t_f	Turn-off Fall Time		-	34	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	100	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	400	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=30A$	-	-	1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F=20A, di/dt=100A/\mu s$	-	15	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	4	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: $T_J=25^\circ C, V_{DD}=15V, V_G=10V, R_G=25\Omega, L=0.5mH, I_{AS}=19.5A$

3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Typical Characteristics

Figure 1: Output Characteristics

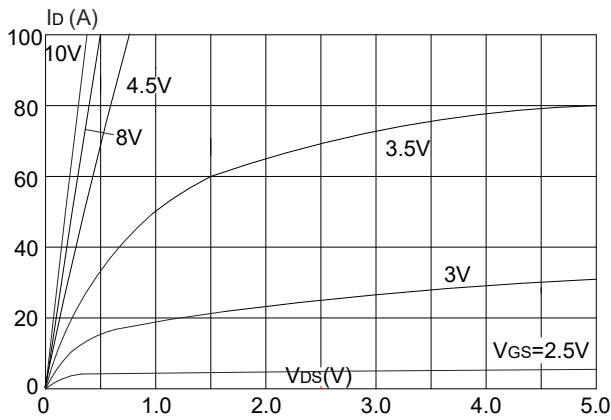


Figure 2: Typical Transfer Characteristics

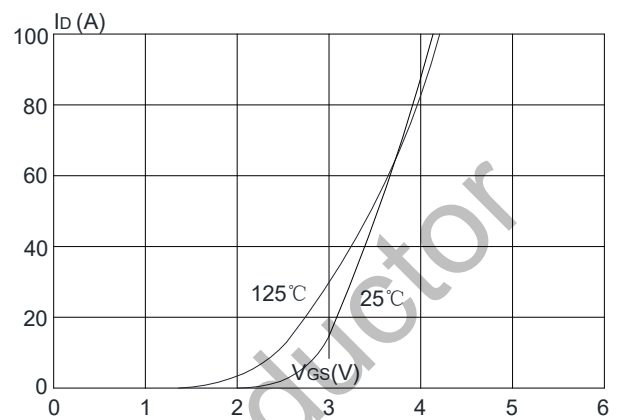


Figure 3: On-resistance vs. Drain Current

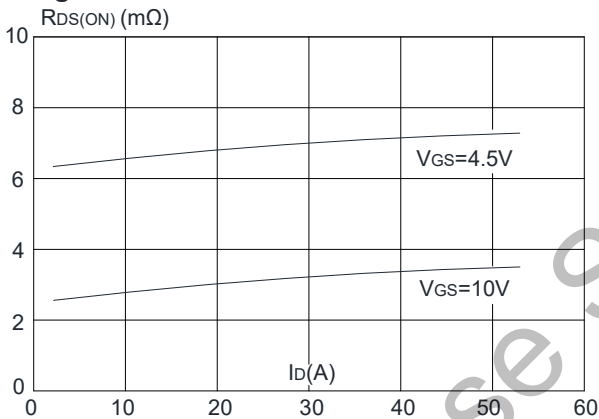


Figure 4: Body Diode Characteristics

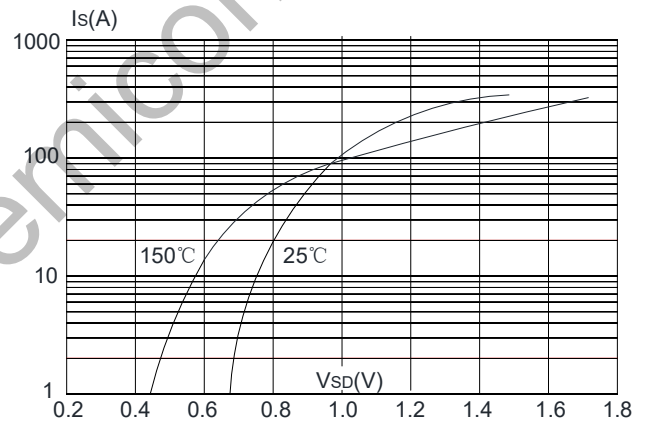


Figure 5: Gate Charge Characteristics

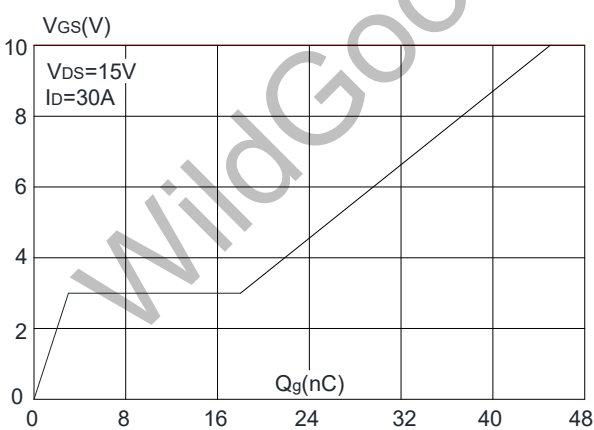


Figure 6: Capacitance Characteristics

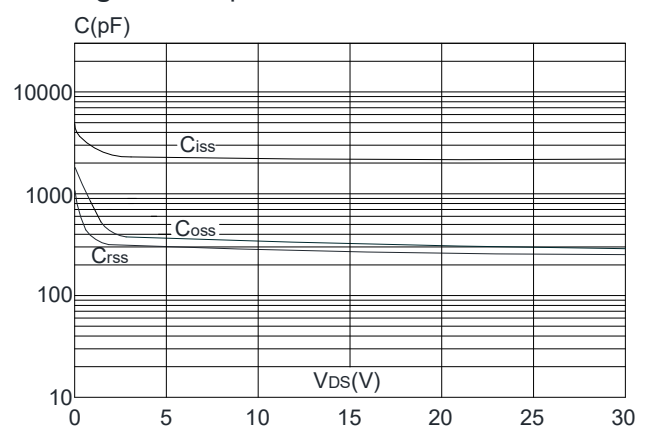


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

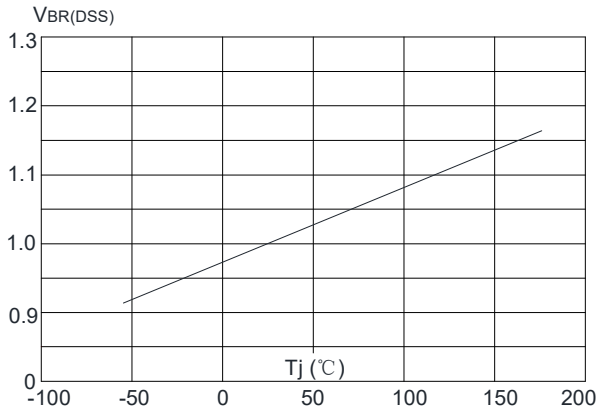


Figure 8: Normalized on Resistance vs. Junction Temperature

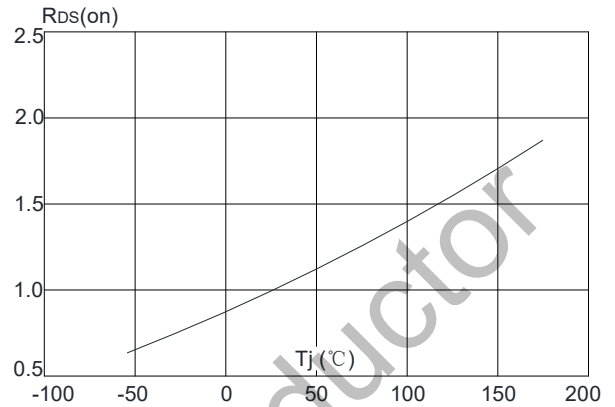


Figure 9: Maximum Safe Operating Area

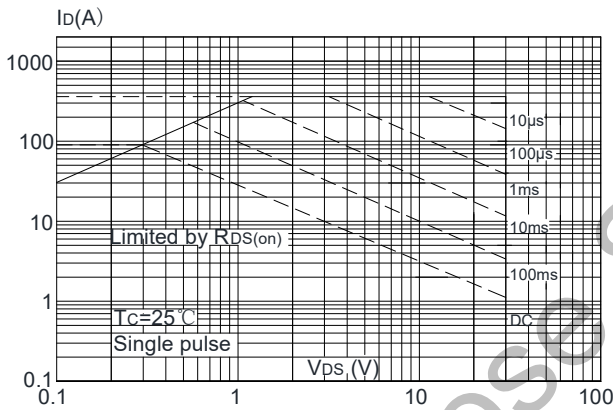
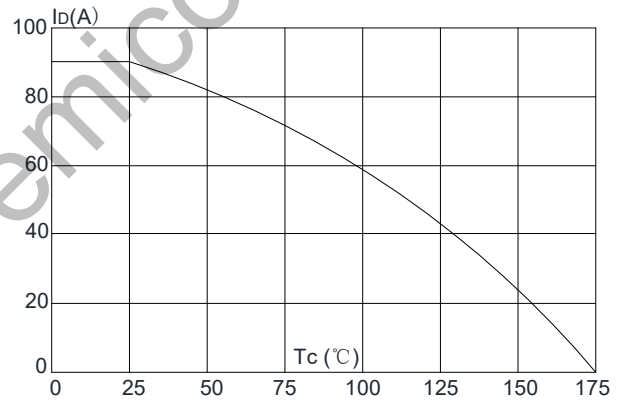
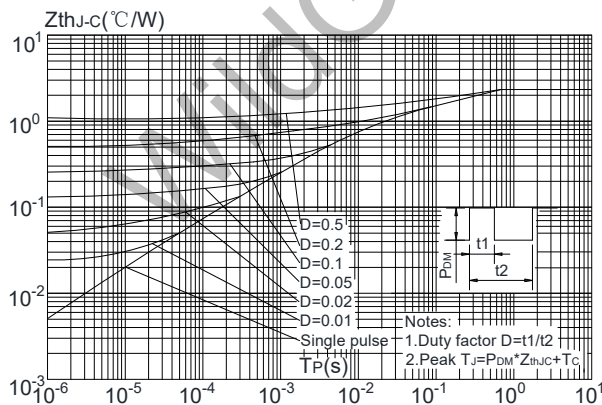


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

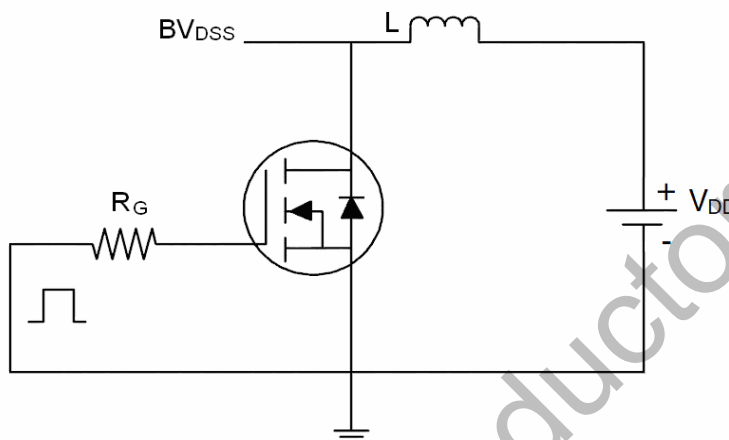


Maximum Effective Transient Thermal Impedance, Junction-to-Case

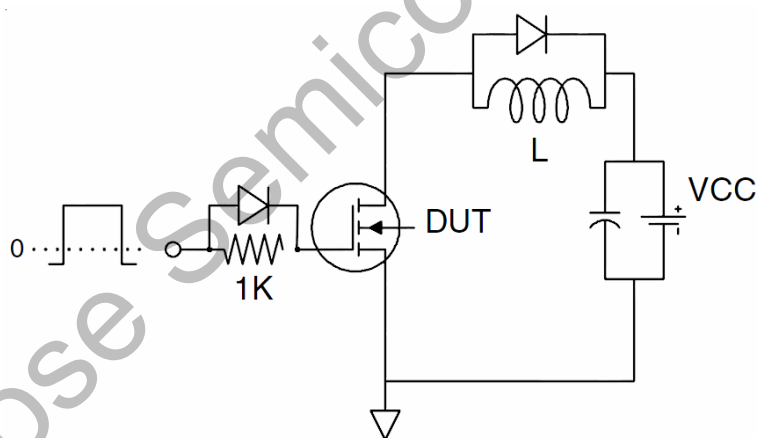


Test Circuit

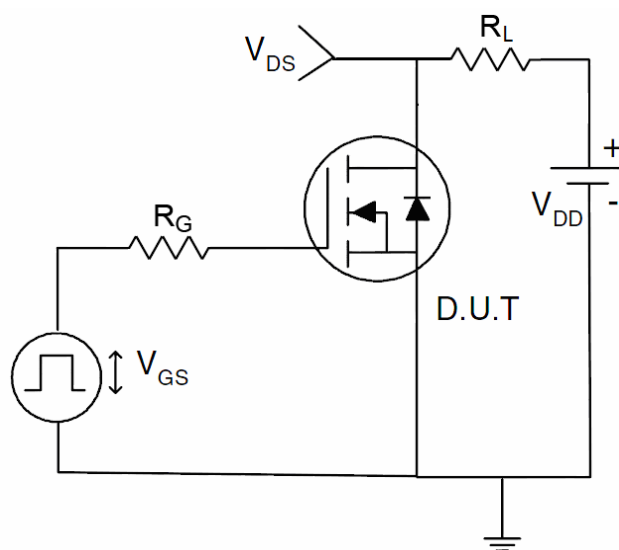
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit:



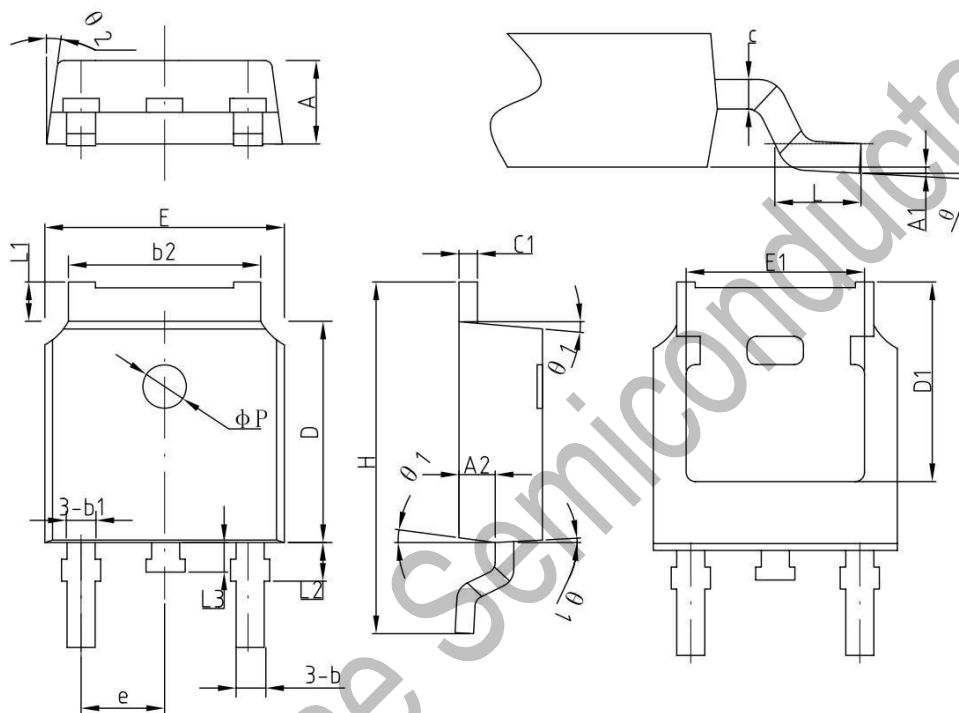
3) Switch Time Test Circuit:



Package Dimension

TO-252

Unit: mm



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	2.2	2.30	2.38
A1	0	—	0.10
A2	0.90	1.01	1.10
b	0.71	0.76	0.86
b1		0.76	
b2	5.13	5.33	5.46
c	0.47	0.50	0.60
c1	0.47	0.50	0.60
D	6.0	6.10	6.20
D1	—	5.30	—
E	6.50	6.60	6.70
E1	—	4.80	—
e	2.286BSC		
H	9.70	10.10	10.40
L	1.40	1.50	1.70
L1	0.90	—	1.25
L2		1.05	
L3		0.8	
φP		1.2	
θ	0°	—	8°
θ 1	5°	7°	9°
θ 2	5°	7°	9°